

wherein said ceramic substrate has a plurality of through holes in which lifter pins for a semiconductor wafer are inserted.

6. (Amended) The ceramic substrate for a semiconductor-producing/examining device according to claim 1,

wherein said conductor is formed in a region up to the position of 60% in a thickness-direction from the face opposite to a wafer treating face of said ceramic substrate.

10. (Amended) The ceramic substrate for a semiconductor-producing/examining device according to claim 7,

wherein a conductor is formed on the face opposite to a wafer treating face.

11. (Amended) The ceramic substrate for a semiconductor-producing/examining device according to claim 7,

wherein said ceramic substrate is used in a temperature range of 100 to 700°C.

12. (Amended) The ceramic substrate for a semiconductor-producing/examining device according to claim 7,

wherein said ceramic substrate has a plurality of through holes in which lifter pins for a semiconductor wafer are inserted.